

Title (en)  
SEMICONDUCTOR MEMORY ELEMENT ARRANGEMENT

Title (de)  
HALBLEITERSPEICHERELEMENTANORDNUNG

Title (fr)  
ENSEMBLE D'ELEMENTS DE MEMOIRE A SEMI-CONDUCTEURS

Publication  
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Application  
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Abstract (en)  
[origin: WO03028107A1] The invention relates to a method for producing a semiconductor memory element arrangement. According to said method, an isolating layer and a layer system consisting of a floating gate and a tunnel barrier arrangement applied to the floating gate are applied to a substrate. A first gate electrode is embodied next to the floating gate and a second gate electrode is embodied next to the tunnel barrier arrangement. Said gate electrodes are formed, in a first trench structure, of parallel first trenches, and in a second trench structure, of parallel second trenches which are perpendicular to the first trenches.

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